

ABSTRACT

[00122] A method for controlling a process for fabricating integrated devices on a substrate. The method includes ex-situ and in-situ measurements of pre-etch and post-etch dimensions for structures formed on the substrate and uses the results of the measurements to adjust process recipes and to control the operational status of etch and external substrate processing equipment. In one exemplary application, the method is used during a multi-pass process for fabricating a capacitive structure of a trench capacitor.